

#### **General Description**

The WSF3089 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSF3089 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline

Absolute Maximum Ratings

- 100% EAS Guaranteed
- Green Device Available

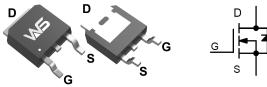
### **Product Summery**

BVDSS	RDSON	ID
30V	4.5mΩ	72A

#### **Applications**

- Synchronous Buck Converter
- DC-DC Power System
- Load Switch

#### **TO-252 Pin Configuration**





#### Symbol Rating Units **Parameter** V $V_{DS}$ Drain-Source Voltage 30 $\pm 20$ $V_{\text{GS}}$ Gate-Source Voltage V Continuous Drain Current,@TC=25°C<sup>1</sup> 72 А $I_D$ Continuous Drain Current, @TC=100°C1 46 А Pulsed Drain Current<sup>2</sup> 200 А $I_{DM}$ EAS Single Pulse Avalanche Energy<sup>3</sup> 80 mJ $\mathbf{P}_{\mathsf{D}}$ W Total Power Dissipation @TC=25°C<sup>4</sup> 50 TSTG °C Storage Temperature Range -55 to 150 $T_{\rm J}$ **Operating Junction Temperature Range** -55 to 150 °C

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>		62	°C/W
R <sub>0JA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup> (t ≤10s)		31	°C/W
R <sub>eJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>		2.5	°C/W



**N-Ch MOSFET** 

#### Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30			V
$\triangle BV_{DSS} / \triangle T_J$	BVDSS Temperature Coefficient	Reference to 25 $^\circ\!\!{\rm C}$ , $I_D$ = 1mA		0.028		V/℃
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =30A		4.5	6.2	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =20A		7.0	9.2	
V <sub>GS(th)</sub>	Gate Threshold Voltage	—V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.1	1.5	2.5	V
$ riangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient			-6.16		mV/℃
	Drain-Source Leakage Current	$V_{DS}$ =24V , $V_{GS}$ =0V , $T_J$ =25 $^\circ \mathrm{C}$			1	uA
I <sub>DSS</sub>		V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55℃			5	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}=\pm20V$ , $V_{DS}=0V$			±100	nA
Qg	Total Gate Charge (4.5V)	V <sub>DS</sub> =15V , V <sub>GS</sub> =10V , I <sub>D</sub> =30A		35		nC
Q <sub>gs</sub>	Gate-Source Charge			6.8		
Q <sub>gd</sub>	Gate-Drain Charge			7.5		
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V , R <sub>G</sub> =6Ω I <sub>D</sub> =15A		11		
Tr	Rise Time			15		ns
T <sub>d(off)</sub>	Turn-Off Delay Time			37.3		
T <sub>f</sub>	Fall Time			10.6		
Ciss	Input Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz		1800		
C <sub>oss</sub>	Output Capacitance			220		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			178		

#### **Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,6</sup>				72	А
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>	$V_G = V_D = 0V$ , Force Current			200	А
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25℃			1.3	V
t <sub>rr</sub>	Reverse Recovery Time			10		nS
Qrr	Reverse Recovery Charge	IF=20A , dI/dt=100A/µs , Tյ=25℃		2.5		nC

Note :

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper,t<10sec.

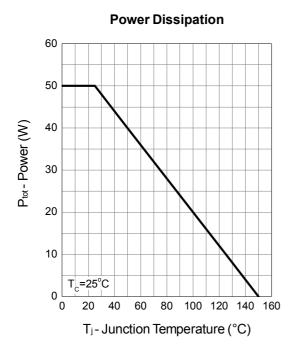
- 2. The data tested by pulsed , pulse width  $\leq 300$ us , duty cycle  $\leq 2\%$ 3. The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=15V,V<sub>GS</sub>=10V,L=0.5mH,I<sub>AS</sub>=18A
- $4. The power dissipation is limited by 175 <math display="inline">^\circ\!\!\!\mathrm{C}$  junction temperature
- 5. The Min. value is 100% EAS tested guarantee.

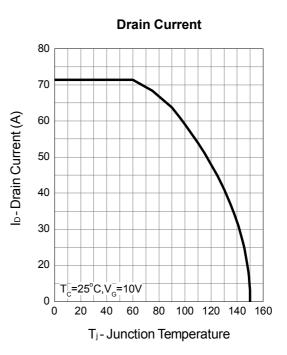
6. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



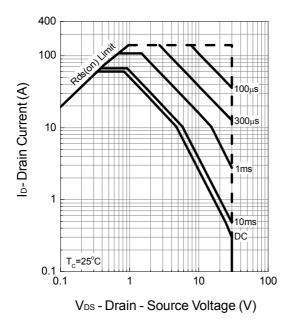
**N-Ch MOSFET** 

## **Typical Operating Characteristics**

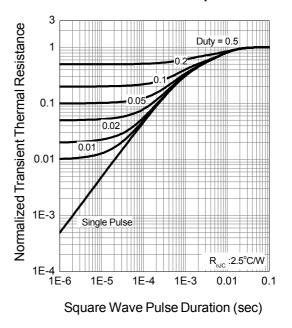




Safe Operation Area



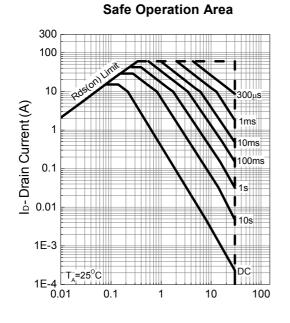
**Thermal Transient Impedance** 





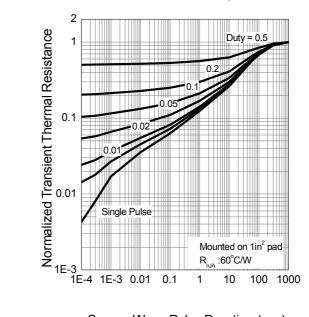
**N-Ch MOSFET** 

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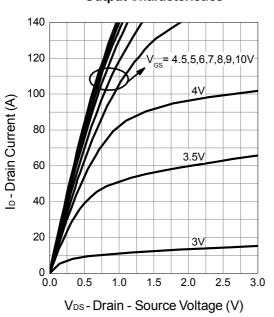


V<sub>DS</sub> - Drain - Source Voltage (V)

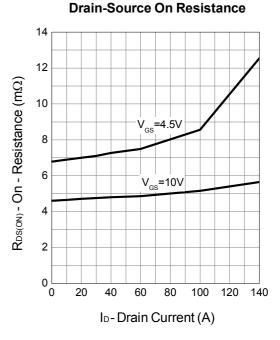
#### **Thermal Transient Impedance**



Square Wave Pulse Duration (sec)



Output Characteristics

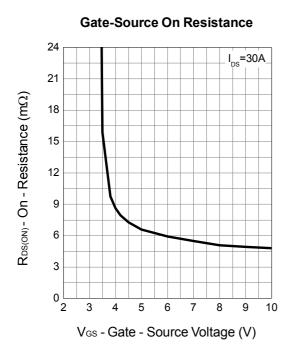


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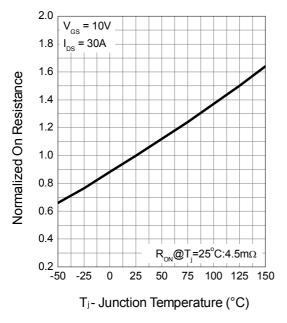


**N-Ch MOSFET** 

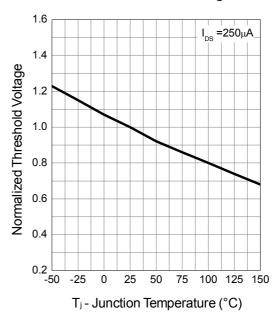
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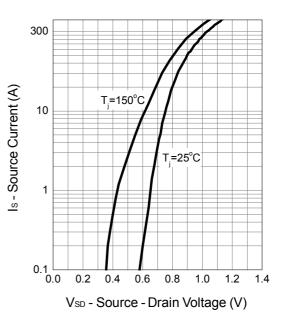
**Drain-Source On Resistance** 



### Gate Threshold Voltage



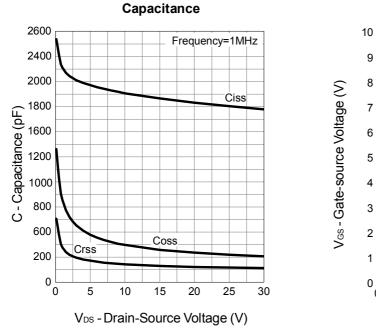
Source-Drain Diode Forward

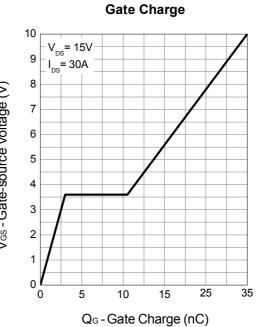




**N-Ch MOSFET** 

# **Typical Operating Characteristics**







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